

Charge Pump DC-to-DC Voltage Converter

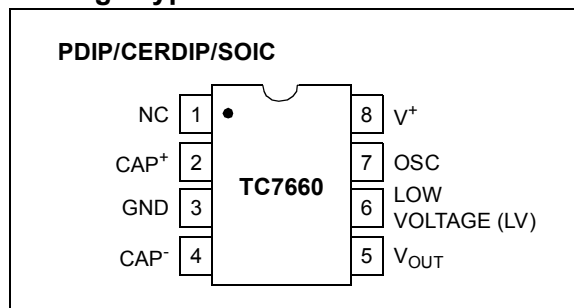
Features

- Wide Input Voltage Range: +1.5V to +10V
- Efficient Voltage Conversion (99.9%, typ)
- Excellent Power Efficiency (98%, typ)
- Low Power Consumption: 80 μ A (typ) @ $V_{IN} = 5V$
- Low Cost and Easy to Use
 - Only Two External Capacitors Required
- Available in 8-Pin Small Outline (SOIC), 8-Pin PDIP and 8-Pin Cerdip Packages
- Improved ESD Protection (3 kV HBM)
- No External Diode Required for High-Voltage Operation

Applications

- RS-232 Negative Power Supply
- Simple Conversion of +5V to $\pm 5V$ Supplies
- Voltage Multiplication $V_{OUT} = \pm n V^+$
- Negative Supplies for Data Acquisition Systems and Instrumentation

Package Types



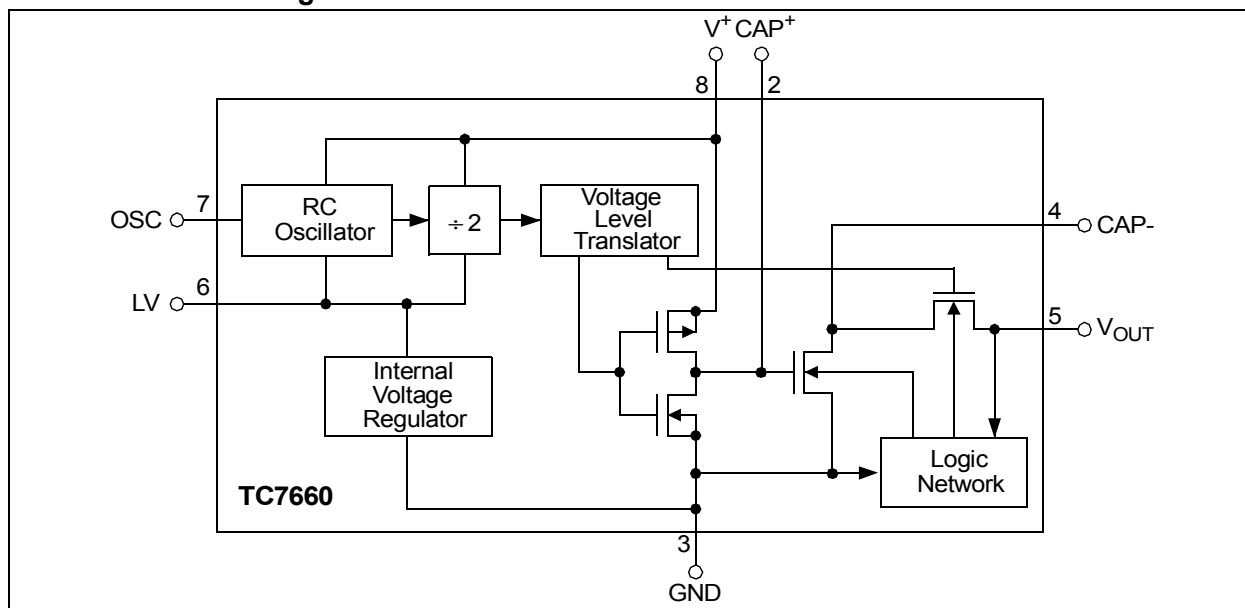
General Description

The TC7660 is a pin-compatible replacement for the industry standard 7660 charge pump voltage converter. It converts a +1.5V to +10V input to a corresponding -1.5V to -10V output using only two low cost capacitors, eliminating inductors and their associated cost, size and electromagnetic interference (EMI).

The on-board oscillator operates at a nominal frequency of 10 kHz. Operation below 10 kHz (for lower supply current applications) is possible by connecting an external capacitor from OSC to ground.

The TC7660 is available in 8-Pin PDIP, 8-Pin Small Outline (SOIC) and 8-Pin Cerdip packages in commercial and extended temperature ranges.

Functional Block Diagram



TC7660

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

Supply Voltage	+10.5V
LV and OSC Inputs Voltage: (Note 1)	
.....	-0.3V to V_{SS} for $V^+ < 5.5V$
.....	$(V^+ - 5.5V)$ to (V^+) for $V^+ > 5.5V$
Current into LV	20 μA for $V^+ > 3.5V$
Output Short Duration ($V_{SUPPLY} \leq 5.5V$).....	Continuous
Package Power Dissipation: ($T_A \leq 70^\circ C$)	
8-Pin CERDIP	800 mW
8-Pin PDIP	730 mW
8-Pin SOIC	470 mW
Operating Temperature Range:	
C Suffix	0°C to +70°C
I Suffix	-25°C to +85°C
E Suffix	-40°C to +85°C
M Suffix	-55°C to +125°C
Storage Temperature Range	-65°C to +160°C
ESD protection on all pins (HBM)	≥ 3 kV
Maximum Junction Temperature	150°C

* **Notice:** Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

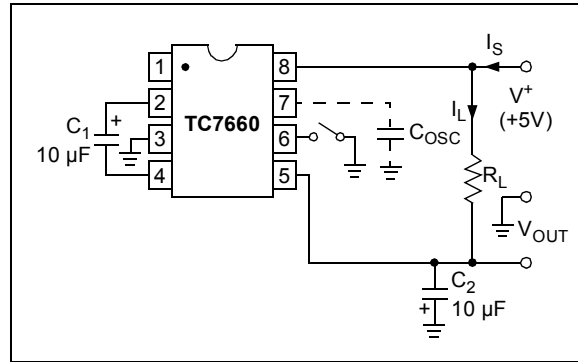


FIGURE 1-1: TC7660 Test Circuit.

ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise noted, specifications measured over operating temperature range with $V^+ = 5V$, $C_{OSC} = 0$, refer to test circuit in Figure 1-1.

Parameters	Sym	Min	Typ	Max	Units	Conditions
Supply Current	I^+	—	80	180	μA	$R_L = \infty$
Supply Voltage Range, High	V^+_H	3.0	—	10	V	$\text{Min} \leq T_A \leq \text{Max}$, $R_L = 10$ k Ω , LV Open
Supply Voltage Range, Low	V^+_L	1.5	—	3.5	V	$\text{Min} \leq T_A \leq \text{Max}$, $R_L = 10$ k Ω , LV to GND
Output Source Resistance	R_{OUT}	—	70	100	Ω	$I_{OUT}=20$ mA, $T_A = +25^\circ C$
		—	—	120		$I_{OUT}=20$ mA, $T_A \leq +70^\circ C$ (C Device)
		—	—	130		$I_{OUT}=20$ mA, $T_A \leq +85^\circ C$ (E and I Device)
		—	104	150		$I_{OUT}=20$ mA, $T_A \leq +125^\circ C$ (M Device)
		—	150	300		$V^+ = 2V$, $I_{OUT} = 3$ mA, LV to GND $0^\circ C \leq T_A \leq +70^\circ C$
		—	160	600		$V^+ = 2V$, $I_{OUT} = 3$ mA, LV to GND $-55^\circ C \leq T_A \leq +125^\circ C$ (M Device)
Oscillator Frequency	f_{OSC}	—	10	—	kHz	Pin 7 open
Power Efficiency	P_{EFF}	95	98	—	%	$R_L = 5$ k Ω
Voltage Conversion Efficiency	V_{OUTEFF}	97	99.9	—	%	$R_L = \infty$
Oscillator Impedance	Z_{OSC}	—	1.0	—	M Ω	$V^+ = 2V$
		—	100	—	k Ω	$V^+ = 5V$

Note 1: Destructive latch-up may occur if voltages greater than V^+ or less than GND are supplied to any input pin.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $C_1 = C_2 = 10 \mu\text{F}$, $\text{ESR}_{C1} = \text{ESR}_{C2} = 1 \Omega$, $T_A = 25^\circ\text{C}$. See Figure 1-1.

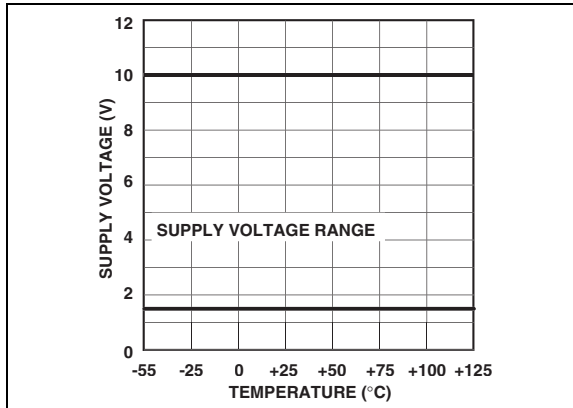


FIGURE 2-1: Operating Voltage vs. Temperature.

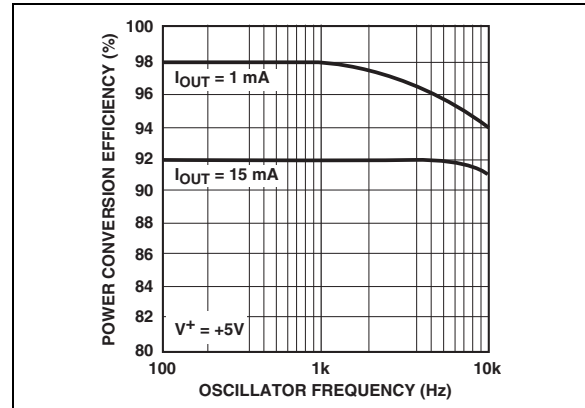


FIGURE 2-4: Power Conversion Efficiency vs. Oscillator Frequency.

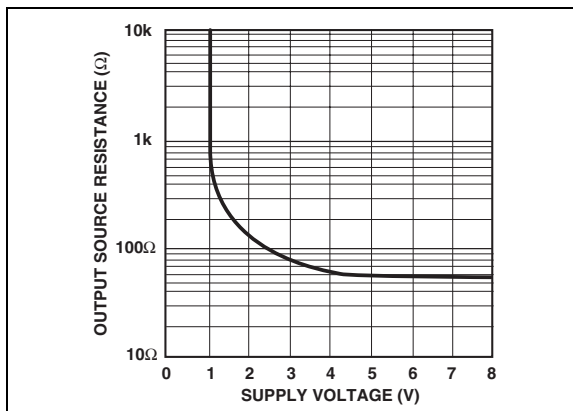


FIGURE 2-2: Output Source Resistance vs. Supply Voltage.

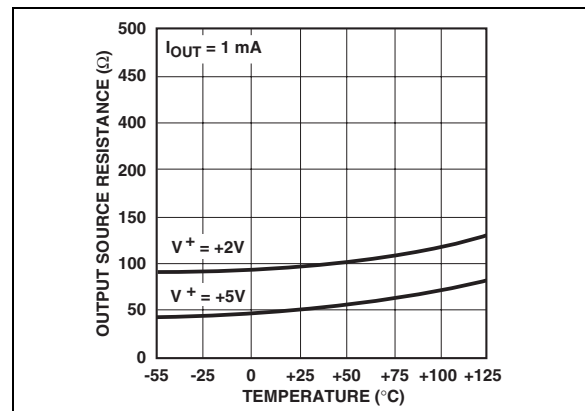


FIGURE 2-5: Output Source Resistance vs. Temperature.

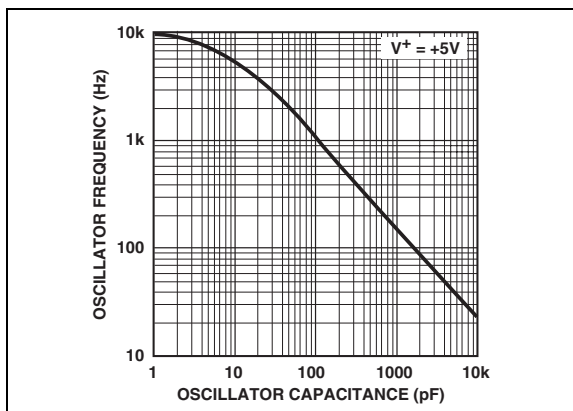


FIGURE 2-3: Frequency of Oscillation vs. Oscillator Capacitance.

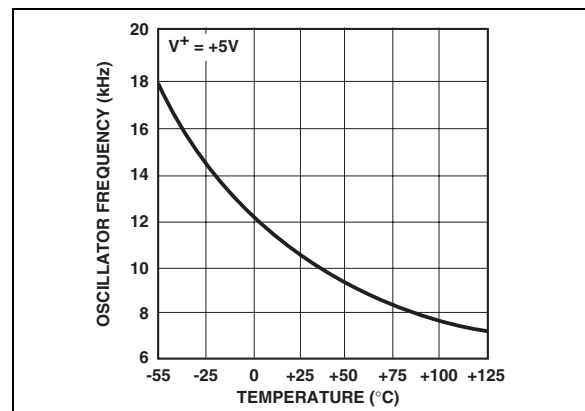


FIGURE 2-6: Unloaded Oscillator Frequency vs. Temperature.

TC7660

Note: Unless otherwise indicated, $C_1 = C_2 = 10 \mu\text{F}$, $\text{ESR}_{C1} = \text{ESR}_{C2} = 1 \Omega$, $T_A = 25^\circ\text{C}$. See Figure 1-1.

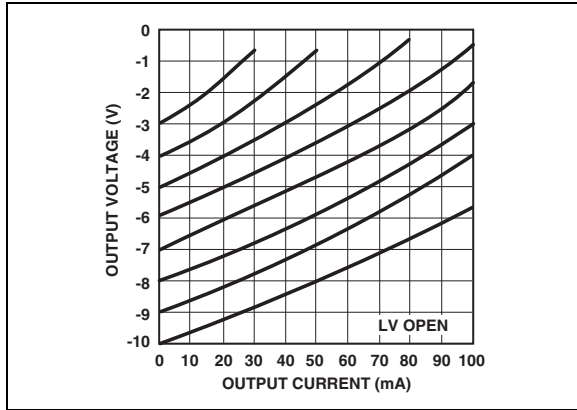


FIGURE 2-7: Output Voltage vs. Output Current.

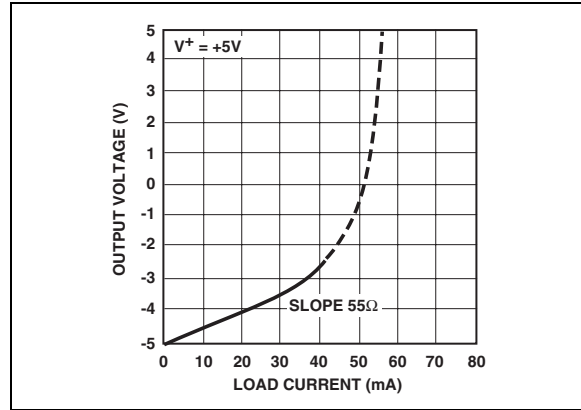


FIGURE 2-10: Output Voltage vs. Load Current.

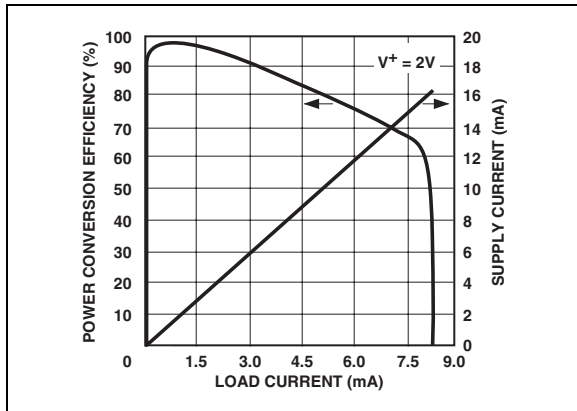


FIGURE 2-8: Supply Current and Power Conversion Efficiency vs. Load Current.

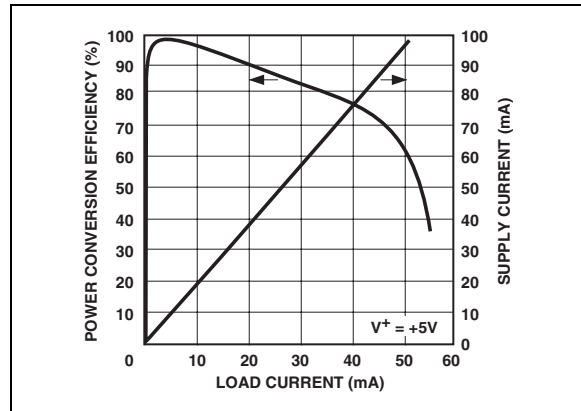


FIGURE 2-11: Supply Current and Power Conversion Efficiency vs. Load Current.

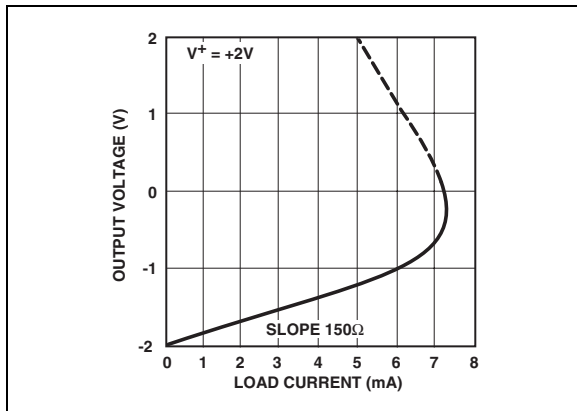


FIGURE 2-9: Output Voltage vs. Load Current.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No.	Symbol	Description
1	NC	No connection
2	CAP ⁺	Charge pump capacitor positive terminal
3	GND	Ground terminal
4	CAP ⁻	Charge pump capacitor negative terminal
5	V _{OUT}	Output voltage
6	LV	Low voltage pin. Connect to GND for V ₊ < 3.5V
7	OSC	Oscillator control input. Bypass with an external capacitor to slow the oscillator
8	V ⁺	Power supply positive voltage input

3.1 Charge Pump Capacitor (CAP⁺)

Positive connection for the charge pump capacitor, or flying capacitor, used to transfer charge from the input source to the output. In the voltage-inverting configuration, the charge pump capacitor is charged to the input voltage during the first half of the switching cycle. During the second half of the switching cycle, the charge pump capacitor is inverted and charge is transferred to the output capacitor and load.

It is recommended that a low ESR (equivalent series resistance) capacitor be used. Additionally, larger values will lower the output resistance.

3.2 Ground (GND)

Input and output zero volt reference.

3.3 Charge Pump Capacitor (CAP⁻)

Negative connection for the charge pump capacitor, or flying capacitor, used to transfer charge from the input to the output. Proper orientation is imperative when using a polarized capacitor.

3.4 Output Voltage (V_{OUT})

Negative connection for the charge pump output capacitor. In the voltage-inverting configuration, the charge pump output capacitor supplies the output load during the first half of the switching cycle. During the second half of the switching cycle, charge is restored to the charge pump output capacitor.

It is recommended that a low ESR (equivalent series resistance) capacitor be used. Additionally, larger values will lower the output ripple.

3.5 Low Voltage Pin (LV)

The low voltage pin ensures proper operation of the internal oscillator for input voltages below 3.5V. The low voltage pin should be connected to ground (GND) for input voltages below 3.5V. Otherwise, the low voltage pin should be allowed to float.

3.6 Oscillator Control Input (OSC)

The oscillator control input can be utilized to slow down or speed up the operation of the TC7660. Refer to Section 5.4, "Changing the TC7660 Oscillator Frequency", for details on altering the oscillator frequency.

3.7 Power Supply (V⁺)

Positive power supply input voltage connection. It is recommended that a low ESR (equivalent series resistance) capacitor be used to bypass the power supply input to ground (GND).

4.0 DETAILED DESCRIPTION

4.1 Theory of Operation

The TC7660 charge pump converter inverts the voltage applied to the V^+ pin. The conversion consists of a two-phase operation (Figure 4-1). During the first phase, switches S_2 and S_4 are open and switches S_1 and S_3 are closed. C_1 charges to the voltage applied to the V^+ pin, with the load current being supplied from C_2 . During the second phase, switches S_2 and S_4 are closed and switches S_1 and S_3 are open. Charge is transferred from C_1 to C_2 , with the load current being supplied from C_1 .

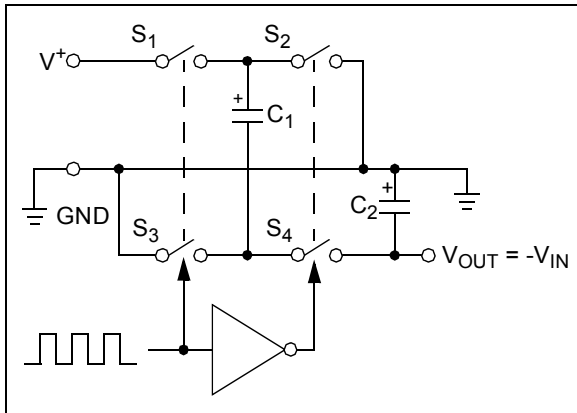


FIGURE 4-1: Ideal Switched Capacitor Inverter.

In this manner, the TC7660 performs a voltage inversion, but does not provide regulation. The average output voltage will drop in a linear manner with respect to load current. The equivalent circuit of the charge pump inverter can be modeled as an ideal voltage source in series with a resistor, as shown in Figure 4-2.

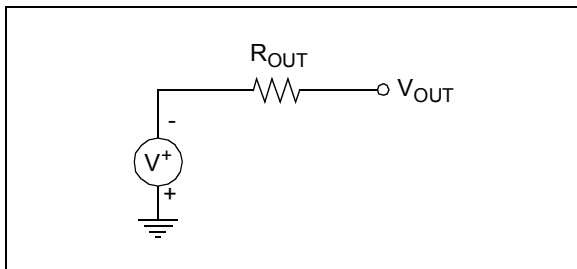


FIGURE 4-2: Switched Capacitor Inverter Equivalent Circuit Model.

The value of the series resistor (R_{OUT}) is a function of the switching frequency, capacitance and equivalent series resistance (ESR) of C_1 and C_2 and the on-resistance of switches S_1 , S_2 , S_3 and S_4 . A close approximation for R_{OUT} is given in the following equation:

EQUATION

$$R_{OUT} = \left[\frac{I}{f_{PUMP} \times C I} + 8R_{SW} + 4ESR_{C1} + ESR_{C2} \right]$$

Where:

$$f_{PUMP} = \frac{f_{OSC}}{2}$$

R_{SW} = on-resistance of the switches

ESR_{C1} = equivalent series resistance of C_1

ESR_{C2} = equivalent series resistance of C_2

4.2 Switched Capacitor Inverter Power Losses

The overall power loss of a switched capacitor inverter is affected by four factors:

1. Losses from power consumed by the internal oscillator, switch drive, etc. These losses will vary with input voltage, temperature and oscillator frequency.
2. Conduction losses in the non-ideal switches.
3. Losses due to the non-ideal nature of the external capacitors.
4. Losses that occur during charge transfer from C_1 to C_2 when a voltage difference between the capacitors exists.

Figure 4-3 depicts the non-ideal elements associated with the switched capacitor inverter power loss.

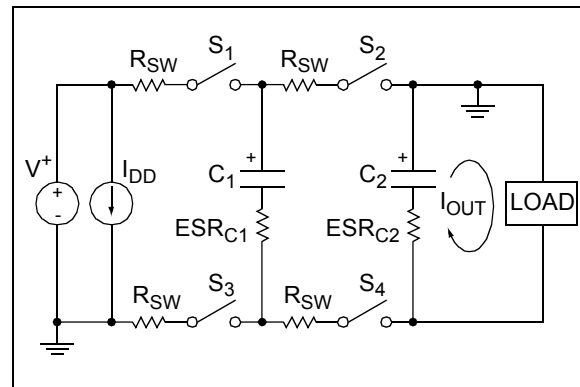


FIGURE 4-3: Non-Ideal Switched Capacitor Inverter.

The power loss is calculated using the following equation:

EQUATION

$$P_{LOSS} = I_{OUT}^2 \times R_{OUT} + I_{DD} \times V^+$$

5.0 APPLICATIONS INFORMATION

5.1 Simple Negative Voltage Converter

Figure 5-1 shows typical connections to provide a negative supply where a positive supply is available. A similar scheme may be employed for supply voltages anywhere in the operating range of +1.5V to +10V, keeping in mind that pin 6 (LV) is tied to the supply negative (GND) only for supply voltages below 3.5V.

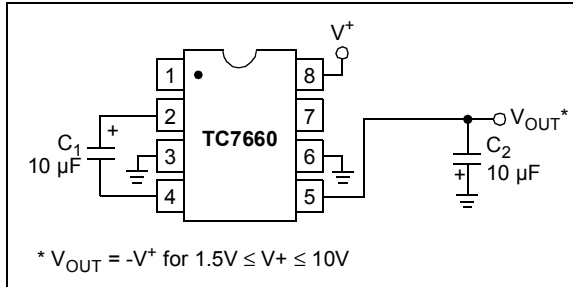


FIGURE 5-1: Simple Negative Converter.

The output characteristics of the circuit in Figure 5-1 are those of a nearly ideal voltage source in series with a 70Ω resistor. Thus, for a load current of -10 mA and a supply voltage of +5V, the output voltage would be -4.3V.

5.2 Paralleling Devices

To reduce the value of R_{OUT} , multiple TC7660 voltage converters can be connected in parallel (Figure 5-2). The output resistance will be reduced by approximately a factor of n , where n is the number of devices connected in parallel.

EQUATION

$$R_{OUT} = \frac{R_{OUT}(of\ TC7660)}{n\ (number\ of\ devices)}$$

While each device requires its own pump capacitor (C_1), all devices may share one reservoir capacitor (C_2). To preserve ripple performance, the value of C_2 should be scaled according to the number of devices connected in parallel.

5.3 Cascading Devices

A larger negative multiplication of the initial supply voltage can be obtained by cascading multiple TC7660 devices. The output voltage and the output resistance will both increase by approximately a factor of n , where n is the number of devices cascaded.

EQUATION

$$V_{OUT} = -n(V^+)$$

$$R_{OUT} = n \times R_{OUT}(of\ TC7660)$$

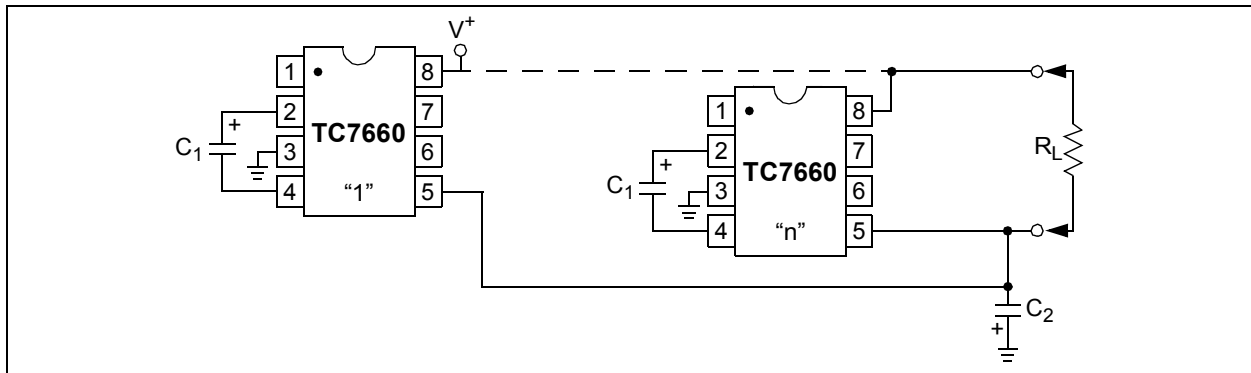


FIGURE 5-2: Paralleling Devices Lowers Output Impedance.

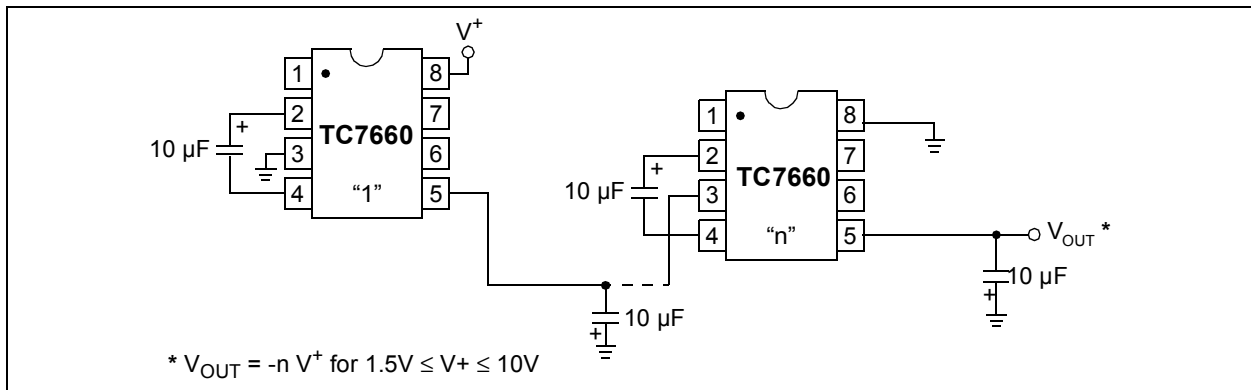


FIGURE 5-3: Increased Output Voltage By Cascading Devices.

5.4 Changing the TC7660 Oscillator Frequency

The operating frequency of the TC7660 can be changed in order to optimize the system performance. The frequency can be increased by over-driving the OSC input (Figure 5-4). Any CMOS logic gate can be utilized in conjunction with a 1 kΩ series resistor. The resistor is required to prevent device latch-up. While TTL level signals can be utilized, an additional 10 kΩ pull-up resistor to V⁺ is required. Transitions occur on the rising edge of the clock input. The resultant output voltage ripple frequency is one half the clock input. Higher clock frequencies allow for the use of smaller pump and reservoir capacitors for a given output voltage ripple and droop. Additionally, this allows the TC7660 to be synchronized to an external clock, eliminating undesirable beat frequencies.

At light loads, lowering the oscillator frequency can increase the efficiency of the TC7660 (Figure 5-5). By lowering the oscillator frequency, the switching losses are reduced. Refer to Figure 2-3 to determine the typical operating frequency based on the value of the external capacitor. At lower operating frequencies, it may be necessary to increase the values of the pump and reservoir capacitors in order to maintain the desired output voltage ripple and output impedance.

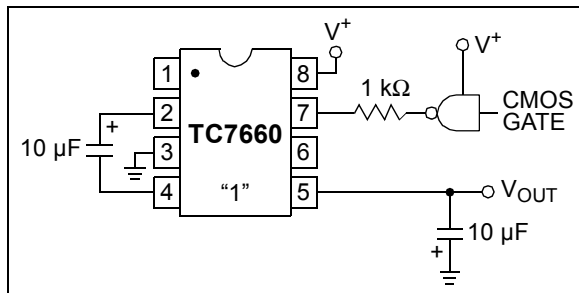


FIGURE 5-4: External Clocking.

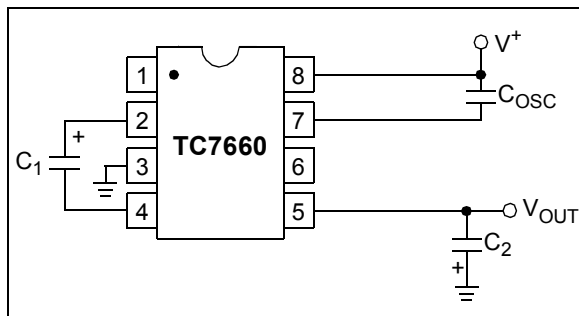


FIGURE 5-5: Lowering Oscillator Frequency.

5.5 Positive Voltage Multiplication

Positive voltage multiplication can be obtained by employing two external diodes (Figure 5-6). Refer to the theory of operation of the TC7660 (Section 4.1). During the half cycle when switch S₂ is closed, capacitor C₁ of Figure 5-6 is charged up to a voltage of V⁺ - V_{F1}, where V_{F1} is the forward voltage drop of diode D₁. During the next half cycle, switch S₁ is closed, shifting the reference of capacitor C₁ from GND to V⁺. The energy in capacitor C₁ is transferred to capacitor C₂ through diode D₂, producing an output voltage of approximately:

EQUATION

$$V_{OUT} = 2 \times V^+ - (V_{F1} + V_{F2})$$

where:

V_{F1} is the forward voltage drop of diode D₁
and
V_{F2} is the forward voltage drop of diode D₂.

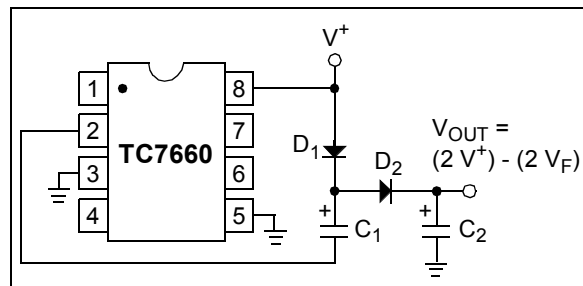


FIGURE 5-6: Positive Voltage Multiplier.

5.6 Combined Negative Voltage Conversion and Positive Supply Multiplication

Simultaneous voltage inversion and positive voltage multiplication can be obtained (Figure 5-7). Capacitors C₁ and C₃ perform the voltage inversion, while capacitors C₂ and C₄, plus the two diodes, perform the positive voltage multiplication. Capacitors C₁ and C₂ are the pump capacitors, while capacitors C₃ and C₄ are the reservoir capacitors for their respective functions. Both functions utilize the same switches of the TC7660. As a result, if either output is loaded, both outputs will drop towards GND.

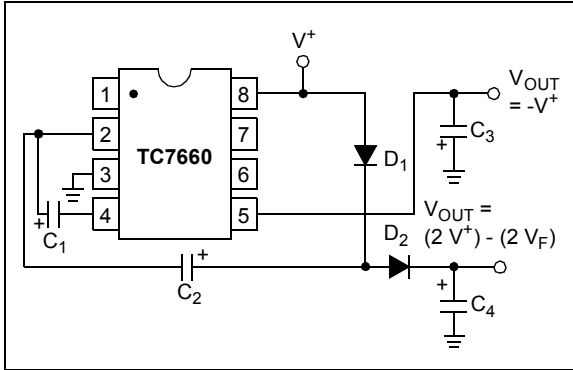


FIGURE 5-7: Combined Negative Converter And Positive Multiplier.

5.7 Efficient Positive Voltage Multiplication/Conversion

Since the switches that allow the charge pumping operation are bidirectional, the charge transfer can be performed backwards as easily as forwards. Figure 5-8 shows a TC7660 transforming $-5V$ to $+5V$ (or $+5V$ to $+10V$, etc.). The only problem here is that the internal clock and switch-drive section will not operate until some positive voltage has been generated. An initial inefficient pump, as shown in Figure 5-7, could be used to start this circuit up, after which it will bypass the other (D_1 and D_2 in Figure 5-7 would never turn on), or else the diode and resistor shown dotted in Figure 5-8 can be used to "force" the internal regulator on.

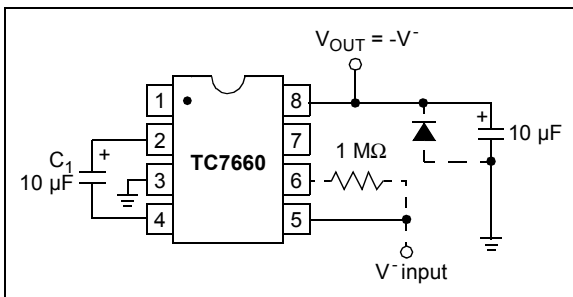


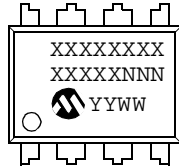
FIGURE 5-8: Positive Voltage Conversion.

TC7660

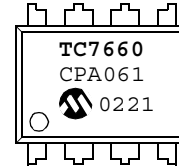
6.0 PACKAGING INFORMATION

6.1 Package Marking Information

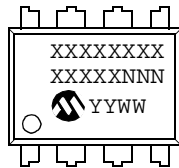
8-Lead PDIP (300 mil)



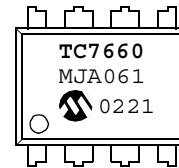
Example:



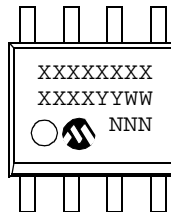
8-Lead CERDIP (300 mil)



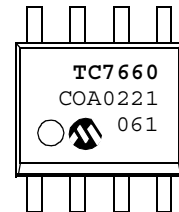
Example:



8-Lead SOIC (150 mil)



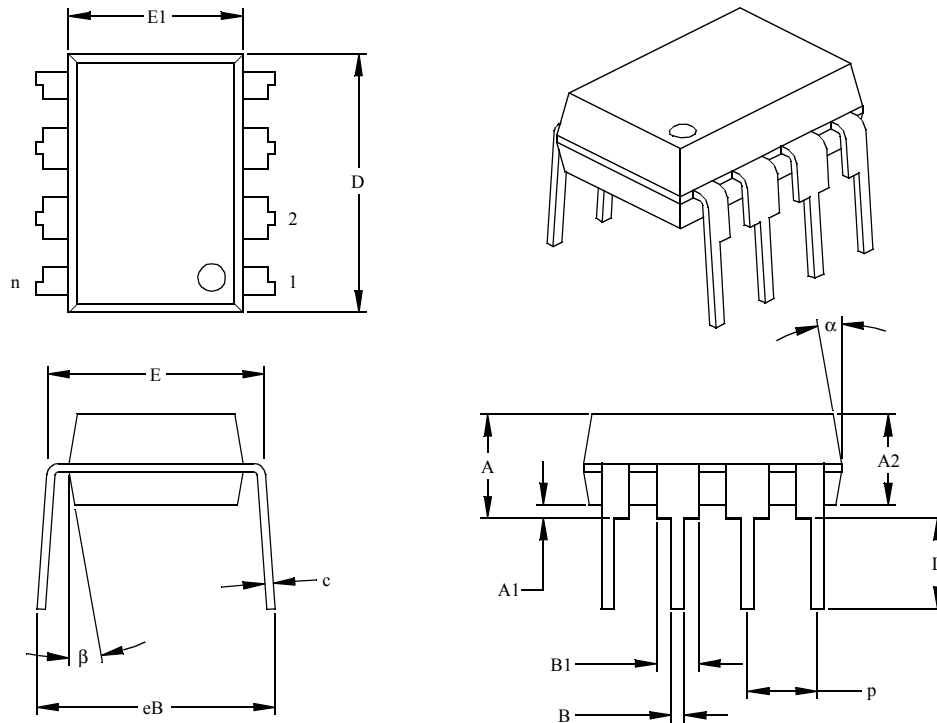
Example:



Legend:	XX...X	Customer specific information*
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
Note:	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line thus limiting the number of available characters for customer specific information.	

* Standard marking consists of Microchip part number, year code, week code, traceability code (facility code, mask rev#, and assembly code). For marking beyond this, certain price adders apply. Please check with your Microchip Sales Office.

8-Lead Plastic Dual In-line (P) – 300 mil (PDIP)



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	E	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	c	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	B	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing	§ eB	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter
 § Significant Characteristic

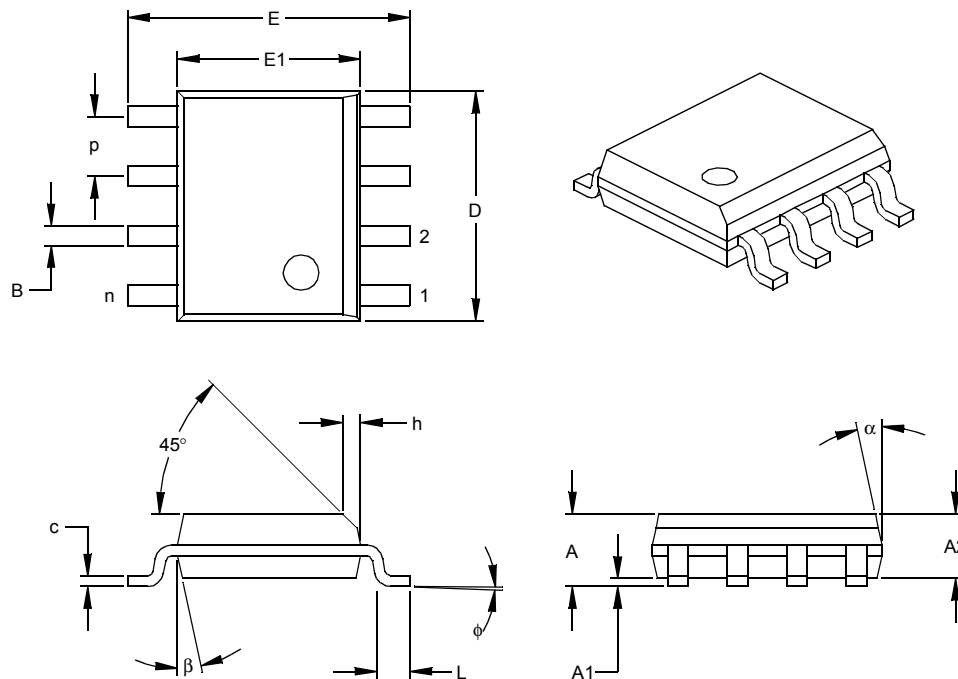
Notes:
 Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.
 JEDEC Equivalent: MS-001
 Drawing No. C04-018

TC7660

8-Lead Ceramic Dual In-line – 300 mil (CERDIP)

Packaging diagram not available at this time.

8-Lead Plastic Small Outline (SN) – Narrow, 150 mil (SOIC)



Dimension Limits	Units	INCHES*			MILLIMETERS		
		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	p		.050			1.27	
Overall Height	A	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	E	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	c	.008	.009	.010	0.20	0.23	0.25
Lead Width	B	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

* Controlling Parameter
 § Significant Characteristic

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC Equivalent: MS-012

Drawing No. C04-057

TC7660

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>X</u>	<u>/XX</u>
Device	Temperature Range	Package
Device:	TC7660:	DC-to-DC Voltage Converter
Temperature Range:	C =	0°C to +70°C
	E =	-40°C to +85°C
	I =	-25°C to +85°C (CERDIP only)
	M =	-55°C to +125°C (CERDIP only)
Package:	PA =	Plastic DIP, (300 mil body), 8-lead
	JA =	Ceramic DIP, (300 mil body), 8-lead
	OA =	SOIC (Narrow), 8-lead
	OA713 =	SOIC (Narrow), 8-lead (Tape and Reel)

Examples:

- a) TC7660COA: Commercial Temp., SOIC package.
- b) TC7660COA713: Tape and Reel, Commercial Temp., SOIC package.
- c) TC7660CPA: Commercial Temp., PDIP package.
- d) TC7660EOA: Extended Temp., SOIC package.
- e) TC7660EOA713: Tape and Reel, Extended Temp., SOIC package.
- f) TC7660EPA: Extended Temp., PDIP package.
- g) TC7660JA: Industrial Temp., CERDIP package
- h) TC7660MJA: Military Temp., CERDIP package.

Sales and Support

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

1. Your local Microchip sales office
2. The Microchip Corporate Literature Center U.S. FAX: (480) 792-7277
3. The Microchip Worldwide Site (www.microchip.com)

Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.

New Customer Notification System

Register on our web site (www.microchip.com/cn) to receive the most current information on our products.

TC7660

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products.

Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, KEELOQ, MPLAB, PIC, PICmicro, PICSTART and PRO MATE are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.


FilterLab, microID, MXDEV, MXLAB, PICMASTER, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

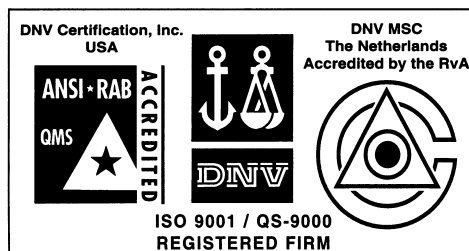
dsPIC, dsPICDEM.net, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, microPort, Migratable Memory, MPASM, MPLIB, MPLINK, MPSIM, PICC, PICDEM, PICDEM.net, rFPIC, Select Mode and Total Endurance are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

Serialized Quick Turn Programming (SQTP) is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2002, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

 Printed on recycled paper.



Microchip received QS-9000 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona in July 1999 and Mountain View, California in March 2002. The Company's quality system processes and procedures are QS-9000 compliant for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, non-volatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001 certified.



MICROCHIP

WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7200 Fax: 480-792-7277
Technical Support: 480-792-7627
Web Address: <http://www.microchip.com>

Rocky Mountain

2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7966 Fax: 480-792-4338

Atlanta

3780 Mansell Road, Suite 130
Alpharetta, GA 30022
Tel: 770-640-0034 Fax: 770-640-0307

Boston

2 Lan Drive, Suite 120
Westford, MA 01886
Tel: 978-692-3848 Fax: 978-692-3821

Chicago

333 Pierce Road, Suite 180
Itasca, IL 60143
Tel: 630-285-0071 Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160
Addison, TX 75001
Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Tri-Atria Office Building
32255 Northwestern Highway, Suite 190
Farmington Hills, MI 48334
Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

2767 S. Albright Road
Kokomo, Indiana 46902
Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

18201 Von Karman, Suite 1090
Irvine, CA 92612
Tel: 949-263-1888 Fax: 949-263-1338

San Jose

Microchip Technology Inc.
2107 North First Street, Suite 590
San Jose, CA 95131
Tel: 408-436-7950 Fax: 408-436-7955

Toronto

6285 Northam Drive, Suite 108
Mississauga, Ontario L4V 1X5, Canada
Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Australia

Microchip Technology Australia Pty Ltd
Suite 22, 41 Rawson Street
Epping 2121, NSW
Australia
Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Microchip Technology Consulting (Shanghai)
Co., Ltd., Beijing Liaison Office
Unit 915
Bei Hai Wan Tai Bldg.
No. 6 Chaoyangmen Beidajie
Beijing, 100027, No. China
Tel: 86-10-85282100 Fax: 86-10-85282104

China - Chengdu

Microchip Technology Consulting (Shanghai)
Co., Ltd., Chengdu Liaison Office
Rm. 2401-2402, 24th Floor,
Ming Xing Financial Tower
No. 88 TIDU Street
Chengdu 610016, China
Tel: 86-28-86766200 Fax: 86-28-86766599

China - Fuzhou

Microchip Technology Consulting (Shanghai)
Co., Ltd., Fuzhou Liaison Office
Unit 28F, World Trade Plaza
No. 71 Wusi Road
Fuzhou 350001, China
Tel: 86-591-7503506 Fax: 86-591-7503521

China - Shanghai

Microchip Technology Consulting (Shanghai)
Co., Ltd.
Room 701, Bldg. B
Far East International Plaza
No. 317 Xian Xia Road
Shanghai, 200051
Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

China - Shenzhen

Microchip Technology Consulting (Shanghai)
Co., Ltd., Shenzhen Liaison Office
Rm. 15-16, 13/F, Shenzhen Kerry Centre,
Renminnan Lu
Shenzhen 518001, China
Tel: 86-755-82350361 Fax: 86-755-82366086

China - Hong Kong SAR

Microchip Technology Hongkong Ltd.
Unit 901-6, Tower 2, Metroplaza
223 Hing Fong Road
Kwai Fong, N.T., Hong Kong
Tel: 852-2401-1200 Fax: 852-2401-3431

India

Microchip Technology Inc.
India Liaison Office
Divyasree Chambers
1 Floor, Wing A (A3/A4)
No. 11, O'Shaughnessy Road
Bangalore, 560 025, India
Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Microchip Technology Japan K.K.
Benex S-1 6F
3-18-20, Shinyokohama
Kohoku-Ku, Yokohama-shi
Kanagawa, 222-0033, Japan
Tel: 81-45-471-6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea
168-1, Youngbo Bldg. 3 Floor
Samsung-Dong, Kangnam-Ku
Seoul, Korea 135-882
Tel: 82-2-554-7200 Fax: 82-2-558-5934

Singapore

Microchip Technology Singapore Pte Ltd.
200 Middle Road
#07-02 Prime Centre
Singapore, 188980
Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan

Microchip Technology (Barbados) Inc.,
Taiwan Branch
11F-3, No. 207
Tung Hua North Road
Taipei, 105, Taiwan
Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Austria

Microchip Technology Austria GmbH
Durisolstrasse 2
A-4600 Wels
Austria
Tel: 43-7242-2244-399
Fax: 43-7242-2244-393

Denmark

Microchip Technology Nordic ApS
Regus Business Centre
Lautrup høj 1-3
Ballerup DK-2750 Denmark
Tel: 45 4420 9895 Fax: 45 4420 9910

France

Microchip Technology SARL
Parc d'Activite du Moulin de Massy
43 Rue du Saule Trapu
Batiment A - 1er Etage
91300 Massy, France
Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Microchip Technology GmbH
Steinheilstrasse 10
D-85737 Ismaning, Germany
Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

Italy

Microchip Technology SRL
Centro Direzionale Colleoni
Palazzo Taurus 1 V. Le Colleoni 1
20041 Agrate Brianza
Milan, Italy
Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom

Microchip Ltd.
505 Eskdale Road
Winkersley Triangle
Wokingham
Berkshire, England RG41 5TU
Tel: 44 118 921 5869 Fax: 44-118 921-5820

11/15/02